

ABSTRACT OF THE DISCLOSURE

This invention provides a pattern formation material for electron beam lithography, which contains an alkali-soluble resin, a photoacid generator, and
5 dissolution inhibiting groups, and also provides a pattern formation method and exposure mask fabrication method using the material. As the dissolution inhibiting groups, this invention uses a first dissolution inhibiting group which increases the
10 sensitivity of the pattern formation material when the material is left to stand in a vacuum after an electron beam irradiation, and a second dissolution inhibiting group which decreases the sensitivity under the same condition. In this invention, the ratio of the first
15 dissolution inhibiting group to the second dissolution inhibiting group is so adjusted that the size of an alkali-soluble portion, which is made soluble in an alkali solution by an electron beam irradiation, is substantially held constant independently of the
20 standing time in a vacuum.